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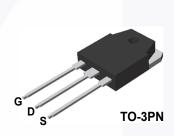
Features

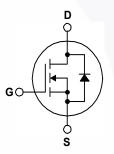
- 24 A, 500 V, $R_{DS(on)}$ = 200 m Ω (Max.) @ V_{GS} = 10 V, I_D = 12 A
- Low Gate Charge (Typ. 90 nC)
- Low Crss (Typ. 55 pF)
- 100% Avalanche Tested
- RoHS compliant

Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switch mode power supply, power factor correction, electronic lamp ballast based on half bridge.





Absolute Maximum Ratings T_c = 25°C unless otherwise noted.

Symbol	Parameter		FQA24N50	Unit	
V _{DSS}	Drain-Source Voltage		500	V	
I _D	Drain Current - Continuous ($T_C = 25^{\circ}C$)		24	A	
	- Continuous (T _C = 100°C)		15.2	A	
DM	Drain Current - Pulsed	(Note 1)	96	A	
V _{GSS}	Gate-Source Voltage		± 30		
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	1100	mJ	
AR	Avalanche Current	(Note 1)	24	A	
E _{AR}	Repetitive Avalanche Energy	(Note 1)	29	mJ	
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	4.5	V/ns	
D	Power Dissipation ($T_C = 25^{\circ}C$)		290	W	
	- Derate above 25°C		2.33	W/°C	
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C	
TL	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds		300	°C	

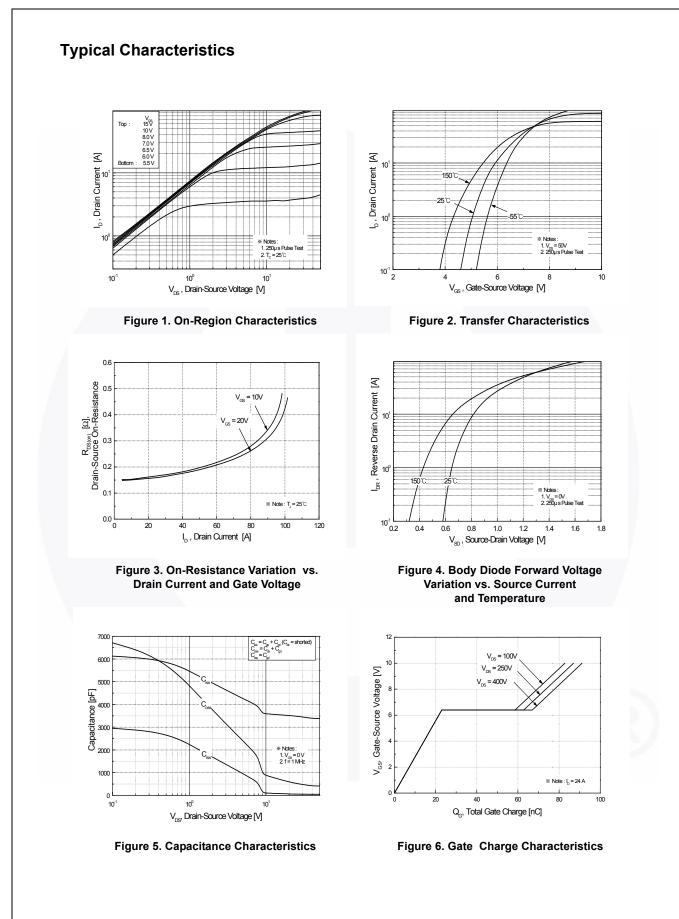
Thermal Characteristics

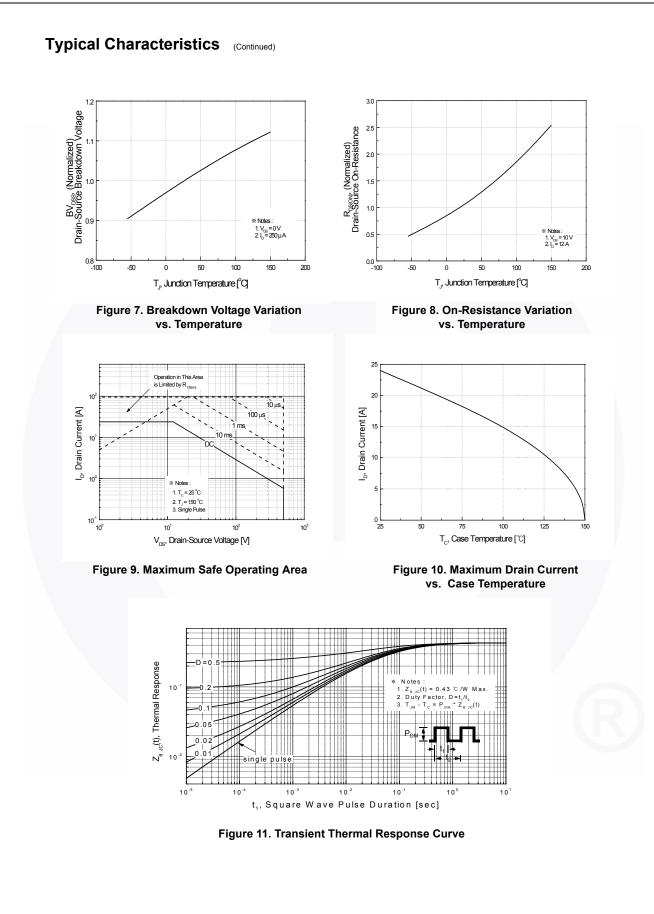
Symbol	Parameter	Тур.	Max.	Unit	
$R_{ extsf{ heta}JC}$	Thermal Resistance, Junction-to-Case		0.43	°C/W	
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink	0.24		°C/W	
R_{\thetaJA}	Thermal Resistance, Junction-to-Ambient		40	°C/W	

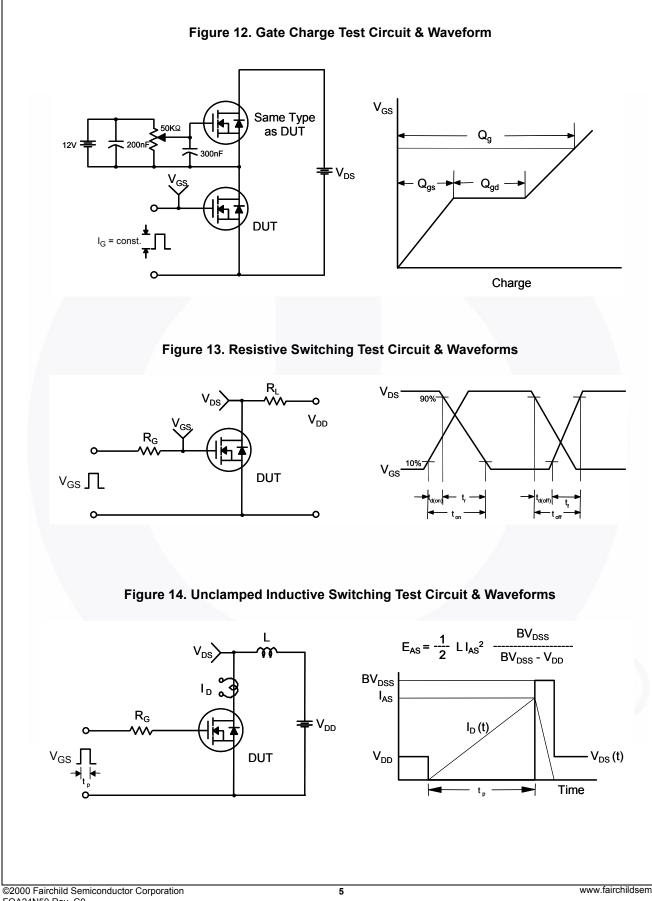
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•		Top Mark	Pack	Package Packing Method Reel Size		Tape Width		ı Qı	Quantity		
			-3PN Tube N/A		N/A			30 units			
Electric	al Char	acteristics $T_c =$	25°C un	less of	herwise note	ed.					
Symbol		Parameter	20 0 0			ondition	S	Min.	Тур.	Max.	Uni
Off Cha	rootoriotic			-							
BV _{DSS}	aracteristics Drain-Source Breakdown Voltage		V _{GS} = 0 V, I _D = 250 μA			500			V		
$\Delta BV_{DSS}/$	Breakdown Voltage Temperature Coeffi-					000					
ΔT_{J}	cient			$I_D = 250 \ \mu A$, Referenced to $25^{\circ}C$					0.53		V/°C
I _{DSS}	Zero Gate Voltage Drain Current			V _{DS} = 500 V, V _{GS} = 0 V						1	μA
			$V_{DS} = 400 \text{ V}, \text{ T}_{C} = 125^{\circ}\text{C}$						10	μA	
I _{GSSF}	Gate-Body Leakage Current, Forward			V _{GS} = 30 V, V _{DS} = 0 V						100	nA
I _{GSSR}	Gate-Body	Leakage Current, Rev	erse	V _{GS}	= -30 V, V _D s	_s = 0 V				-100	nA
On Cha	racteristic	s									
V _{GS(th)}	Gate Threshold Voltage $V_{DS} = V_{GS}$, $I_D = 25$				250 µA		3.0		5.0	V	
R _{DS(on)}	Static Drain On-Resista	n-Source			= 10 V, I _D =				0.156	0.2	Ω
9 _{FS}	Forward Tr	ansconductance		V _{DS}	= 50 V, I _D =	12 A			22		S
C _{iss}	c Charact			V _{DS}	= 25 V, V _{GS}	= 0 V,			3500	4500	pF
C _{oss}	Output Ca	pacitance		f = 1	I.0 MHz		-		520	670	pF
C _{rss}	Reverse T	ransfer Capacitance							55	70	pF
Switchi	ng Charao	teristics									
t _{d(on)}	Turn-On D					04.4			80	170	ns
t _r	Turn-On R	ise Time			$V_{DD} = 250 \text{ V}, \text{ I}_{D} = 24 \text{ A},$ R _G = 25 Ω		-		250	500	ns
t _{d(off)}	Turn-Off D	elay Time		'`G	20 32		F		200	400	ns
t _f	Turn-Off Fa	all Time		(Note 4)		(Note 4)		155	320	ns	
Qg	Total Gate	Charge		VDS	= 400 V, I _D :	= 24 A,			90	120	nC
Q _{gs}	Gate-Sour	ce Charge			5		-		23		nC
Q _{gd}	Gate-Drain	Charge		(Note 4)		(Note 4)		44		nC	
Q _{gs} Q _{gd}				V _{GS} = 10 V (Note 4)			(Note 4)				
	1	de Characteristic				ngs				0.1	
l _S	Maximum Continuous Drain-Source Diode Forward Current								24	A	
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current							96	A		
V _{SD}		ce Diode Forward Volta	age	$V_{GS} = 0 V, I_S = 24 A$						1.4	V
t _{rr}		ecovery Time		$V_{GS} = 0 V, I_S = 24 A,$		-		400		ns	
Q _{rr}	Reverse R	ecovery Charge		alF	/ dt = 100 A/µ	15			4.3		μC







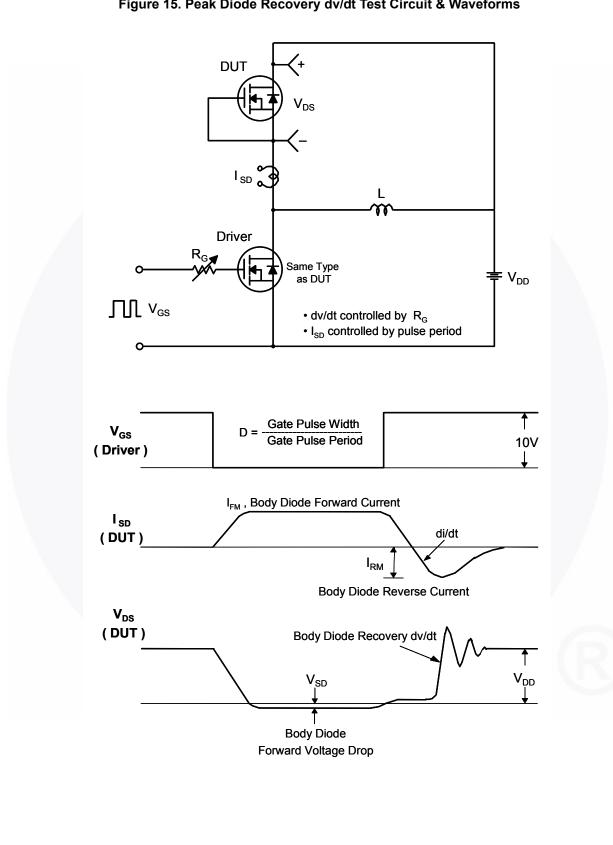
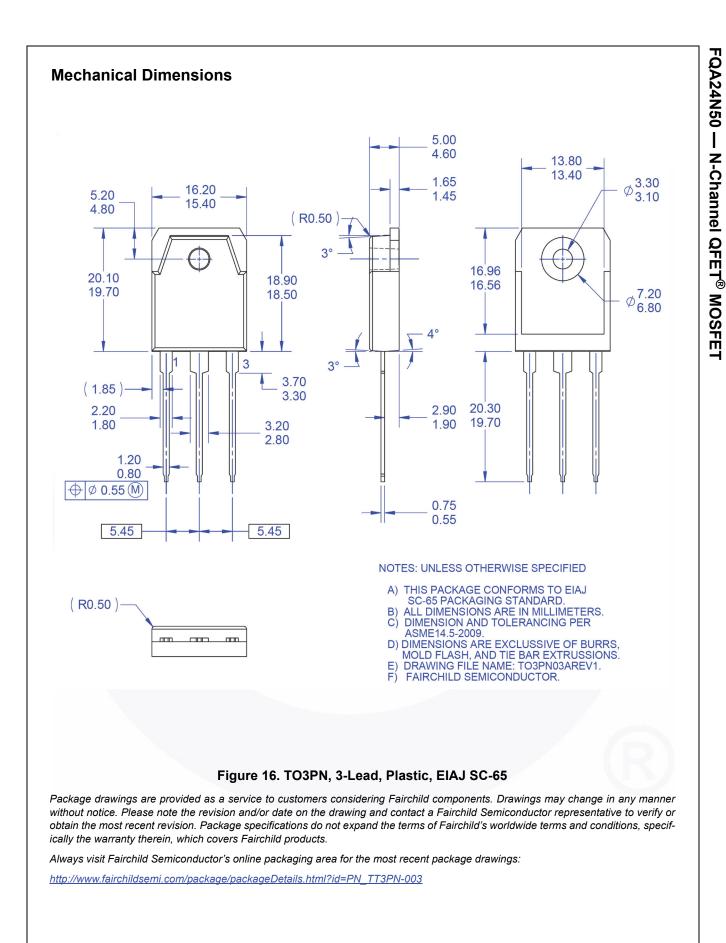


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms





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